HiPerFRED

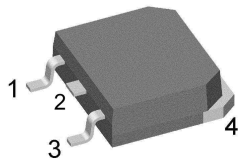
V_{RRM}	=	600 V
I_{FAV}	=	60 A
t_{rr}	=	35 ns

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Single Diode

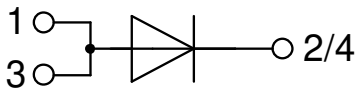
Part number

DSEP60-06AT

Marking on Product: DSEP60-06AT



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-268AA (D3Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

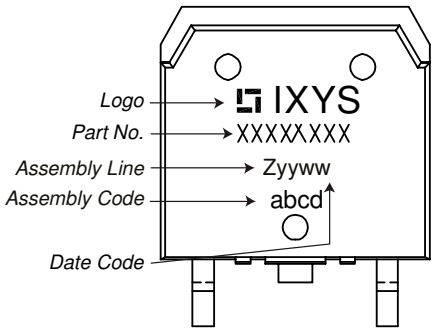
Fast Diode

Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			600	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			600	V
I_R	*reverse current, drain current*	V_R = 600 V	T_{VJ} = 25°C			650	µA
		V_R = 600 V	T_{VJ} = 150°C			2.5	mA
V_F	*forward voltage drop*	I_F = 60 A	T_{VJ} = 25°C			2.04	V
		I_F = 120 A				2.33	V
		I_F = 60 A	T_{VJ} = 150°C			1.39	V
		I_F = 120 A				1.70	V
I_{FAV}	*average forward current*	T_C = 130°C	T_{VJ} = 175°C			60	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 175°C			0.95	V
r_F	*slope resistance* }					5	mΩ
R_{thJC}	*thermal resistance junction to case*					0.45	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.15		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			330	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			600	A
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		67		pF
I_{RM}	*max. reverse recovery current*		T_{VJ} = 25°C		8		A
		I_F = 60 A; V_R = 300 V	T_{VJ} = 100°C		13		A
t_{rr}	*reverse recovery time*	$-di_F/dt$ = 200 A/µs	T_{VJ} = 25°C		35		ns
			T_{VJ} = 100°C		110		ns

Package TO-268AA (D3Pak)			Ratings			
Symbol	**Definition**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal [1)]			70	A
T_{VJ}	*virtual junction temperature*		-55		175	°C
T_{op}	*operation temperature*		-55		150	°C
T_{stg}	*storage temperature*		-55		150	°C
Weight				5		g
F_C	*mounting force with clip*		20		120	N

[1)] I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking

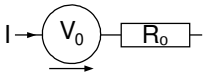


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP60-06AT-TUB	DSEP60-06AT	Tube	30	509748

Similar Part	Package	Voltage class
DSEP60-06A	TO-247AD (2)	600
DHG60I600HA	TO-247AD (2)	600
DPH30IS600HI	ISOPLUS247 (2)	600

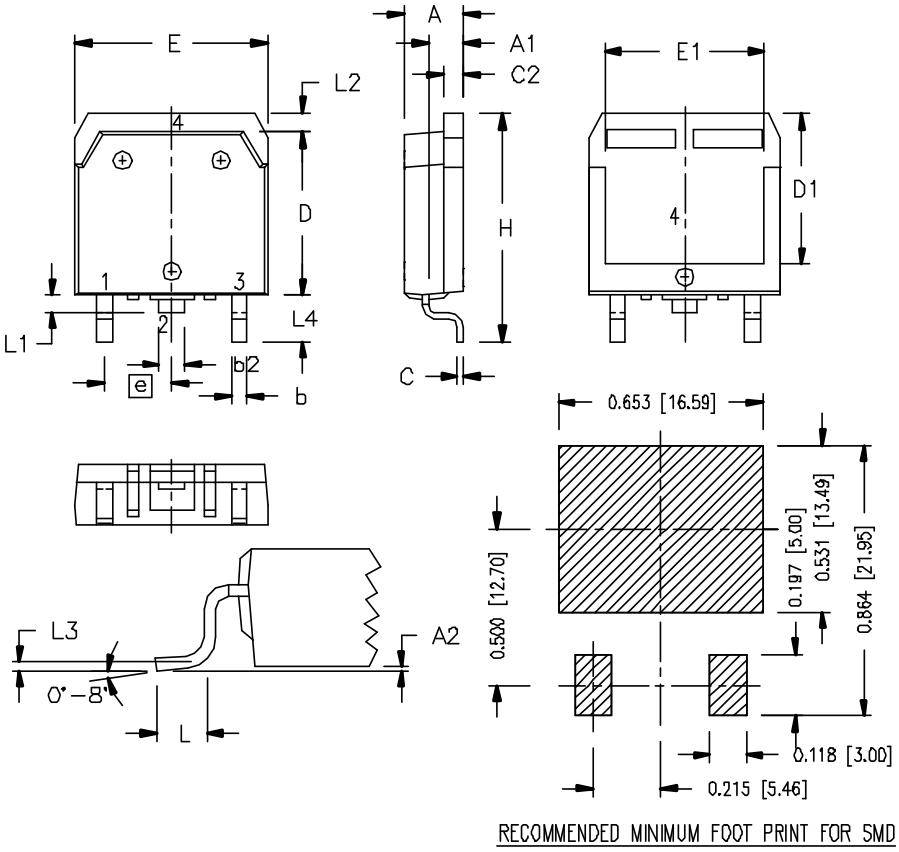
Equivalent Circuits for Simulation

** on die level* T_{VJ} = 175 °C

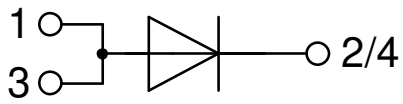


		Fast Diode	
$V_{0\,max}$	*threshold voltage*	0.95	V
$R_{0\,max}$	*slope resistance **	2.4	mΩ

Outlines TO-268AA (D3Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.90	5.10	0.193	0.201
A1	2.70	2.90	0.106	0.114
A2	0.02	0.25	0.001	0.100
b	1.15	1.45	0.045	0.057
b2	1.90	2.10	0.075	0.083
C	0.40	0.65	0.016	0.026
C2	1.45	1.60	0.057	0.063
D	13.80	14.00	0.543	0.551
D1	12.40	12.70	0.488	0.500
E	15.85	16.05	0.624	0.632
E1	13.30	13.60	0.524	0.535
e	5.45 BSC		0.215 BSC	
H	18.70	19.10	0.736	0.752
L	2.40	2.70	0.094	0.106
L1	1.20	1.40	0.047	0.055
L2	1.00	1.15	0.039	0.045
L3	0.25 BSC		0.100 BSC	
L4	3.80	4.10	0.150	0.161



Fast Diode

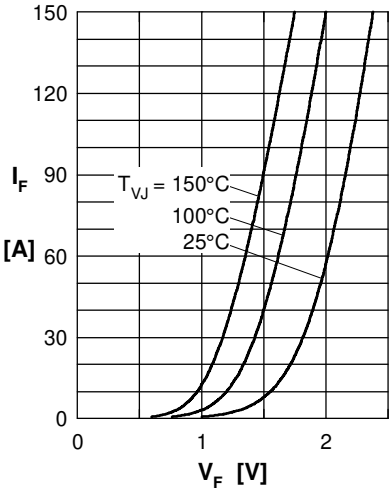


Fig. 1 Forward current I_F versus V_F

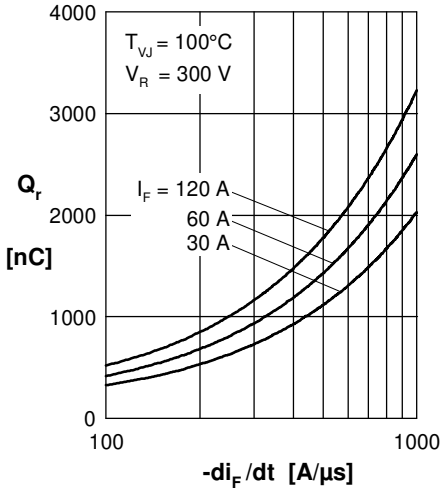


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

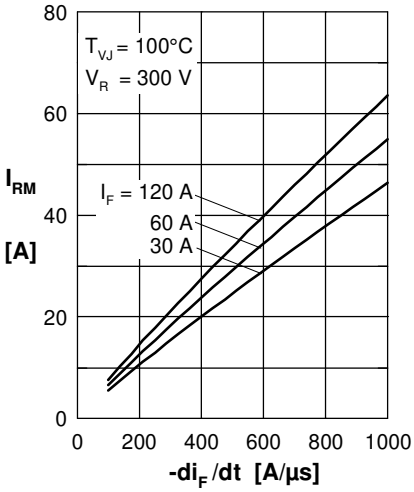


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

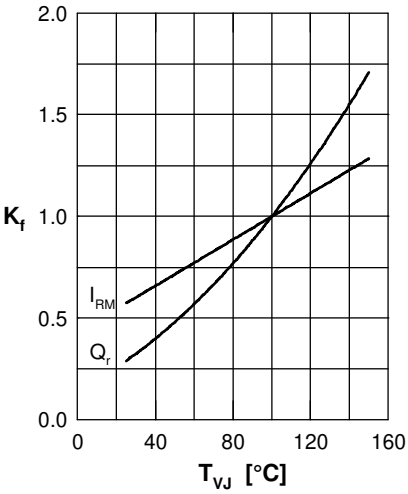


Fig. 4 Typ. dynamic parameters Q_r, I_{RM} versus T_{VJ}

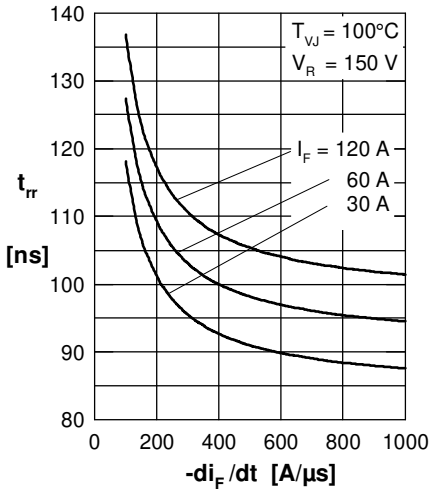


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

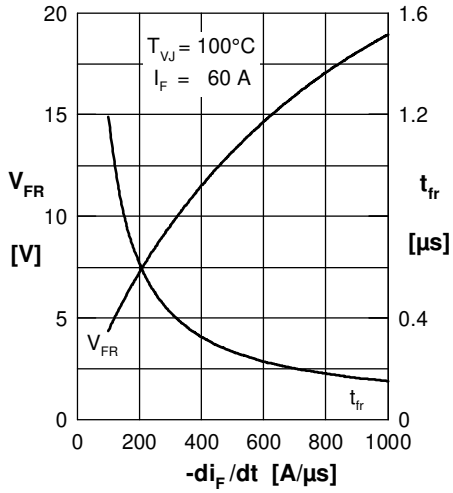


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

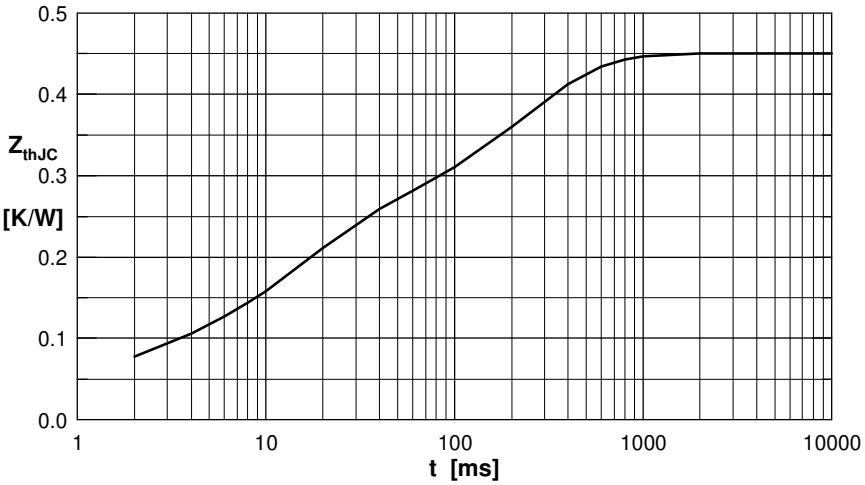


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0050	0.0001
2	0.0550	0.0010
3	0.1750	0.0140
4	0.2150	0.2300